

Drafts Pending Active

- L1: (82) (fin adj field adj effect adj transistor) or finfet
- L2: (32) 1 and trench\$2
- L3: (25) 2 and (grow\$3 or regrow\$3)
- L4: (4) 2 and trench\$2.clm.
- L5: (13) 1 and (trench\$2 or hole\$1 or via\$1).clm.

Failed

Saved

- (0) ("(thin adj film) nearresistor").PN.
- (0) ("(thin adj film) nearresistor").PN.
- (150130) thin adj film
- (14857) (thin adj film) and resistor
- (2054) ((thin adj film) and resistor) and ((thin adj film) ne
- (1735) (((thin adj film) and resistor) and ((thin adj film) ne
- (801) (((((thin adj film) and resistor) and ((thin adj film) ne
- (499) (((((thin adj film) and resistor) and ((thin adj film) ne
- (124) ((((((thin adj film) and resistor) and ((thin adj film) ne
- (34) ((((((thin adj film) and resistor) and ((thin adj film) ne
- (98) (((((thin adj film) and resistor) and ((thin adj film) ne

Favorites

Document ID	Title	Current CR	Current XN	Retrieval	Inventor	C	R	S	M
US 20040048424	Method of forming an N channel and P channel F semiconductor device	438/154			Wu, Chung Cheng et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 20040046227	Semiconductor device	257/500			Ono, Mizuki et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 20040036118	Concurrent Fin-FET and thick-body device fabrication	257/347			Abadeer, Wagdi W. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 20030141569	Fin-type resistors	257/536	257/379; 257/E21.00		Fried, David M. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 6720231 B2	Fin-type resistors	438/382	257/722; 438/238;		Fried, David M. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 6709982 B1	Double spacer FinFET formation	438/696	438/304; 438/596		Buynoski, Matthew S. et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 6706571 B1	Method for forming multilevel structures in	438/157	438/283; 438/236		Yu, Bin et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 6580137 B2	Damascene double gated transistors and related	257/401	257/407; 257/E21.40		Perke, Stephen A.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 6525403 B2	Semiconductor device having MIS field effect	257/618	257/329; 257/330;		Inaba, Satoshi et al.	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 6521502 B1	Solid phase epitaxy activation process for	438/305	438/528		Yu, Bin	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
US 6403434 B1	Process for manufacturing MOS trans	438/300	257/E21.16	61	Yu, Bin	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

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